3mm Silicon PD Chip datasheet

P/N : WS9Z-01C

Application

Si PIN photodiode chips

Structure

Planar type : PIN diode

Electrodes :

Top side (Cathode) : Al

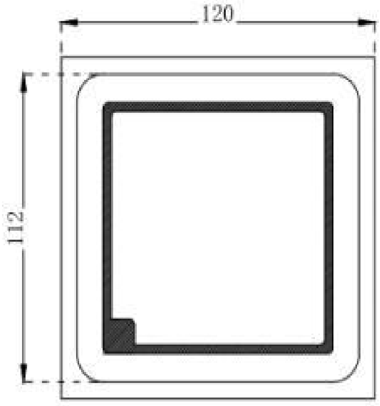
Backside (Anode) : Au Alloy

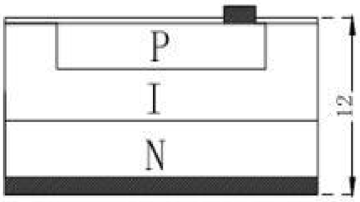
DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	112mil × 112mil (±0.5mil)			mil
Chip width	120mil × 120mil (± 1.5mil)			mil
Chip length	120mil × 120mil (± 1.5mil)			mil
Chip height	12mil ± (1.0mil)			mil
Pad N(Cathode)	6mil (±0.2mil)			mil
Pad P(Anode)	6mil (±0.2mil)			mil

Electro-Optical Characteristics (@ Ta=25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=10mA, H=0	0.5		1.3	V
Reverse Voltage	VBR	IR=100μA, H=0	35			V
Reverse Dark Current	ID	VR=10V, H=0			10	nA
Sensitive Wavelength Range	λp			525		nm
Capacitance	CJ	VR=5V, F=1 MHz		16		pF





Unit : mil

武汉万赢半导体科技有限公司
WUHAN WING CHIP SEMICONDUCTOR TECHNOLOGY Co.,LTD.